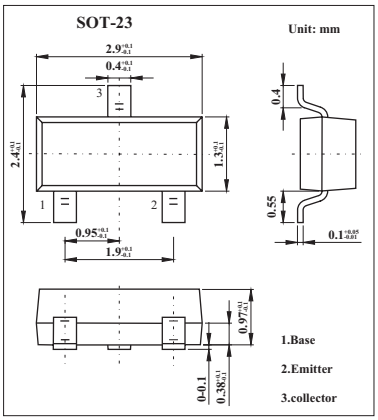
Silicon NPN Epitaxial

2SC4366



■ Features

● Low Frequency amplifier.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	15	V
Collector current	I_C	300	mA
Collector dissipation	P_C	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = 10μA , I_E = 0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 1mA , R_{BE} = ∞	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E = 10μA , I_C = 0	15			V
Collector cutoff current	I_{CBO}	V_{CB} = 50V, I_E=0			1	μA
Base-emitter voltage	V_{BE}	V_{CE} = 6V , I_C = 1mA			0.75	V
DC current gain	h_{FE}	V_{CE} = 6V , I_C = 100mA	800		2000	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 300mA , I_B = 30mA			0.3	V

■ Marking

Marking	ZI-